## Small Signal Fast Switching Diode

## Features

- These diodes are also available in other case styles including the DO35 case with the type designation 1N4148, the MiniMELF case with the type
 designation LL4148, and the SOT23 case with the type designation IMBD4148-V
- Silicon epitaxial planar diode

- Fast switching diodes
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC


## Mechanical Data

Case: SOD323 plastic case
Weight: approx. 4.3 mg
Packaging Codes/Options:
GS18/10 k per 13" reel (8 mm tape), 10 k/box
GS08/3 k per 7" reel (8 mm tape), $15 \mathrm{k} / \mathrm{box}$

Parts Table

| Part | Ordering code | Type Marking | Remarks |
| :---: | :---: | :---: | :---: |
| 1N4148WS-V | 1N4148WS-V-GS18 or 1N4148WS-V-GS08 | A2 | Tape and Reel |

## Absolute Maximum Ratings

$\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Reverse voltage |  | $\mathrm{V}_{\mathrm{R}}$ | 75 | V |
| Repetitive peak reverse voltage | $\mathrm{f} \geq 50 \mathrm{~Hz}$ | $\mathrm{~V}_{\mathrm{RRM}}$ | 100 | V |
| Average rectified current half <br> wave rectification with resistive <br> load |  | $\mathrm{I}_{\mathrm{F}(\mathrm{AV})}$ | mA |  |
| Surge forward current | $\mathrm{t}<1 \mathrm{~s}$ and $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ | $\mathrm{I}_{\mathrm{FSM}}$ | $150^{1)}$ |  |
| Power dissipation |  | $\mathrm{P}_{\text {tot }}$ | 350 | mA |

Note:
${ }^{1)}$ Valid provided that electrodes are kept at ambient temperature.

## 1N4148WS-V

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## Thermal Characteristics

$\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Thermal resistance junction to ambient air |  | $\mathrm{R}_{\text {thJA }}$ | $650^{1)}$ | $\mathrm{K} / \mathrm{W}$ |
| Junction temperature |  | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | $\mathrm{T}_{\text {stg }}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |  |

Note:
${ }^{1)}$ Valid provided that electrodes are kept at ambient temperature.

## Electrical Characteristics

$\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Forward voltage | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$ | $V_{F}$ |  |  | 1000 | mV |
|  | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ | $\mathrm{V}_{\mathrm{F}}$ |  |  | 1200 | mV |
| Leakage current | $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ |  |  | 25 | nA |
|  | $\mathrm{V}_{\mathrm{R}}=75 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ |  |  | 5 | $\mu \mathrm{A}$ |
|  | $\mathrm{V}_{\mathrm{R}}=100 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ |  |  | 100 | $\mu \mathrm{A}$ |
|  | $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}, \mathrm{~T}_{\mathrm{j}}=150{ }^{\circ} \mathrm{C}$ | $\mathrm{I}_{\mathrm{R}}$ |  |  | 50 | $\mu \mathrm{A}$ |
| Diode capacitance | $\mathrm{V}_{\mathrm{F}}=\mathrm{V}_{\mathrm{R}}=0 \mathrm{~V}$ | $\mathrm{C}_{\mathrm{D}}$ |  |  | 4 | pF |
| Voltage rise when switching ON (tested with 50 mA pulses) | tested with 50 mA pulses, $t_{p}=0.1 \mu \mathrm{~s}$, rise time $<30 \mathrm{~ns}$, $\mathrm{f}_{\mathrm{p}}=(5$ to 100$) \mathrm{kHz}$ | $\mathrm{V}_{\mathrm{fr}}$ |  |  | 2.5 | V |
| Reverse recovery time | $\begin{gathered} \mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{R}}=1 \mathrm{~mA}, \mathrm{~V}_{\mathrm{R}}=6 \mathrm{~V}, \\ \mathrm{R}_{\mathrm{L}}=100 \Omega \end{gathered}$ | $\mathrm{t}_{\mathrm{rr}}$ |  |  | 4 | ns |
| Rectification efficiency | $\mathrm{f}=100 \mathrm{MHz}, \mathrm{V}_{\mathrm{RF}}=2 \mathrm{~V}$ | $\eta \nu$ | 0.45 |  |  |  |

## Rectification Efficiency Measurement Circuit



## Typical Characteristics

$\mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$, unless otherwise specified


Figure 1. Forward characteristics


Figure 2. Dynamic Forward Resistance vs. Forward Current


Figure 4. Relative Capacitance vs. Reverse Voltage


Figure 5. Leakage Current vs. Junction Temperature


Figure 3. Admissible Power Dissipation vs. Ambient Temperature


Figure 6. Admissible Repetitive Peak Forward Current vs. Pulse Duration

Package Dimensions in millimeters (inches): SOD323


Rev. 03 - Date: 08. November 2004
Document no.: S8-V-3910.02-001 (4)
17443

## Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.
It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).
The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.
Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.
3. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
4. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
5. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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